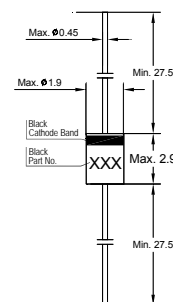


1N4531, 1N4532

Silicon Epitaxial Planar Switching Diode

Applications

- High-speed switching



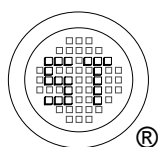
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Current	I_{FSM}	at $t = 1\text{ }\mu\text{s}$	4
		at $t = 1\text{ ms}$	1
		at $t = 1\text{ s}$	0.5
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	200	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 200	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	1	V
Reverse Current	I_R	at $V_R = 20\text{ V}$ 1N4531	25 nA
		at $V_R = 50\text{ V}$ 1N4532	100 nA
		at $V_R = 20\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ 1N4531	50 μA
		at $V_R = 50\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ 1N4532	100 μA
Diode Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_d	1N4531	4 pF
		1N4532	2 pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $I_R = 60\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}	1N4531	4 ns
		1N4532	2 ns
		1N4532	4 ns
at $I_F = 10\text{ mA}$, $I_R = 10\text{ mA}$, $R_L = 100\text{ }\Omega$			



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